		F	TANTA UNIVERSITY FACULTY OF SCIENCE ARTMENT OF CHEMISTRY	
	FI	NAL EXAMINATION	I for Special Chemistry & Materi	al Science Groups
1000	COURSE TITLE:	COURSE CODE: CH 4105		
DATE:	25 JAN 2023	TERM: FIRST	TOTAL ASSESSMENT MARKS: 50 DEGREE	TIME ALLOWED: 2 HOURS

1) Write the name & structure of monomers for each of the following polymers:

(10 marks, 2 marks for each)

- a) Polycarbonate,
- b) Aliphatic polyamide,
- c) Poly(vinyl chloride),
- d) Polyurethanes,
- e) Epoxy resin.
- 2) Write short notes on the following:

(10 marks, 5 marks for each)

- a) Suspension polymerization techniques,
- b) Phenol-formaldehyde resin.
- 3) How can you prepare the following:

(10 marks, 5 marks for each)

- a) Ion exchange resins,
- b) Block copolymers.
- 4) Write short notes on the following:

(10 marks, 5 marks for each)

- a) Vulcanized rubber,
- b) Isomerization polymerization.
- 5) Choose the correct answers:

(10 marks, one mark for each)

- i) What is the name of the organic compound used to prevent the polymerization of the monomers during storage?
 - a) Accelerator,
 - b) Initiator,
 - c) Inhibitor.
- ii) What are the monomers used for the formation of Bakelite?
 - a) Urea & formaldehyde,
 - b) Melamine & formaldehyde,
 - c) Phenol & formaldehyde.
- iii) What is the type of the initiator used in cationic polymerizations?

- a) Acid,
- b) Base,
- c) Free radical.
- iv) Which of the following is common anionic initiator?
 - a) Benzoyl peroxide,
 - b) Azobisisobutyronitrile,
 - c) Na-metal.
- v) What are the monomers used for the formation of polyurethanes?
 - a) Isobutylene & isoprene,
 - b) Diisocyanate & diol,
 - c) Diisocyanate & diamine.
- vi) What is the type of the polymerization of styrene with BuLi?
 - a) Ring-opening polymerization,
 - b) Condensation polymerization,
 - c) Living polymerization.
- vii) Which is the characteristic of cross-linked polymers?
 - a) Melting on heating,
 - b) Insoluble in all solvent,
 - c) Soluble in organic solvent.
- viii) Which is true regarding addition polymerization?
 - a) Monomers contain three functional groups,
 - b) Monomers contain two functional groups,
 - c) Monomers contain olefinic groups.
- ix) What is the type of the polymerization used for the formation of polystyrene?
 - a) Condensation polymerization,
 - b) Addition polymerization,
 - c) Stepwise polymerization.
- x) Which is the characteristic of thermoplastic s?
 - a) Can be molded,
 - b) Cross-linking between chains,
 - c) Can not be melted.

With best regards,



Tanta University – Faculty of Science – Chemistry Department Final Exam for Fourth year students (Chemistry, Material Science Section)

Code: CH4123 Course Title: Industrial Chemistry

January 2023

Note: Exam consists of 6 pages

Date: 28/12/2022

Total Assessment Marks: 100

Time Allowed: 2 h

Part I: Organic Industrial Chemistry (50 Marks) تصحيح إليكتروني

	Ch	oose the correct ansi	wer:	<u>-</u> _						
	For	maldehyde is as a feedst	ock f	or industry						
	a.	dyes	b.	detergents	c.	Plastic	d,	explosives	· · · · · · · · · · · · · · · · · ·	e inggoradinga
2.	Del	nydrogenation of methar	ol by	catalytic oxidation is an	indu	strial method for the ma	nufa	cture of		
	a.	Methane	b.	formalin	c.	ethanol	d.	acetic acid		
3.	Cyc	clohexanone is a starting tramadol	mate b.	erial for the synthesis of aspirin		prilocaine	d.	sildenafil	* * *	47 (F)
١.	Liq	uefied petroleum gases	(LPG) consists of	m	ixture				
	a.	pentane and propane			c.	propane and hexane				
	b.	propane and butane			d.	butane and pentane			a j	
5.		are unstable and	also	mprove the anti-knock to	endei	ncies of gasoline				
	a.	Olefins			c.	Sulfur Compounds				
	b.	Paraffins			d.	Aromatics	9%	er, er ir -	\$. F 4	an greye
ó.	Syn	nthesis gas is a mixture o	of							
	a.	CO ₂ & H ₂ O	b.	NH ₃ & O ₂	c.	H ₂ & CO	d.	H ₂ & NH ₃		
7.	Ace	etylation of p-aminopher	nol gi	ves		K 0		x 5 8 =	ź.	
	a.	Pethidine	b.	Paracetamol	c.	Novocain	d.	Aspirin		
3.	Det	ermining the amount of	hydr	ogen required for a comp	ounc	d to be converted into a s	atura	ted		
	a.	acid hydrolysis			c.	saponification Value				
	b.	cracking test			d.	unsaturation test			8 6 V	7.550 F
).		is the most com	non :	solvent used for vegetabl	e oil	extraction				
	a.	Ethyl acetate	b.	Hexane	c.	Ethanol	d.	Methanol		
	ACM\$	A CONTRACTOR OF THE PARTY OF TH	200505	environd State State Andrews	0.0070				(a) (b) (b)	
				ىقحە	ب الص	من فضلك إقا				

10.	Ble	aching process in oil ext	ractio	on is carried out using				
12.	a.	activated clay	9 (1 ×		c.	hydroperoxide		
	b.	sodium hydroxide			d.	mineral acids		
11.		is the milligrams	of po	ot. hydroxide required to	conv	ert one gram of fat into g	glyce	rin and salt
(#) B	a.	Unsaturation number	8 -		c.	Saponification process		
	b.	Iodine number			d.	Saponification number		
12.		action of ethyl-4-aminol shod for the preparation of			ıo)-et	hanol in presence of so	odiun	n ethoxide is a synthetic
	a.	Novocain	b.	Aspirin	C.	Prilocaine	d.	Lidocaine
13.	Oct	ane number could be cal	culat	ed using as st	anda	rd mixture		
	a.	n-heptane and iso-octar	ņe		c.	n-octane and benzene		
	b.	n-heptane and iso-hept	ane		d.	n-octane and n-hexane		
14.	In t	he synthesis of tolycaine	, the	used amine compound is				
	a.	triethyl amine		methyl amine	c.	diethyl amine	d.	pyridine
15.		is an undesirable		ponent in petroleum bec	ause	of its strong offensive of	dor	
	a.	Oxygen	b.	Nitrogen	c.	Acetylene	d.	Sulphur
16.	In s	oap manufacturing proce	ess,	is added as wa	ter so	ftener		
	a.	brine solution			c.	sodium carboxymethyl	cellu	lose
	b.	zeolite			d.	linear alkylbenzene sul	phoni	ic acid
17.	In v	egetable oil extraction, s	olver	nt extraction method is ap	pplie	d to seeds with low oil co	onten	t such as
	a	soybeans	b.	olive oil	c.	sunflower	d.	sesame oil
18.	One	stage in vegetable oil pr	oces	sing				
	a.	sulphonation	b.	spray drying	c.	degumming	d.	slurry making
19.	One	of the most common oil	s use	d for soap manufacturing	g is .			
	a.	corn oil	b.	coconut oil	c.	sesame oil	d.	sunflower oil
				صفحه	قلب الد	من فضلك إ		

20.	Whe	en 2,6 dimethylaniline	reacts	with chloroacetyl chlori	ide fo	llowed by reaction with	dieth	yl amine g	gives			
	a.	pethidine	b.	Lidocaine	c.	cocaine	d.					
								¥1 (2	9, 22	VV	Section 20	,:// _e
21.	The	spent lye in soap manu	ufactui	ing process is	•							
	a.	brine solution layer			c.	brine/NaOH layer						
	b.	NaOH/H ₂ O layer			d.	brine/glycerin layer						
22.	Sulp	ohapyrimidine is used a	as					+ (2 ₄) 2 ₄	ector: 0	5° × °° ·		rep
	a.	antibacterial agent			c.	anticancer agent						
	b.	anesthetic agent			d.	anti-inflammatory age	nt					
.3. In	veget	table oil extraction, Na	OH is	used for					4 -4			
	a.	separation of glycerol	l		c.	soap formation						
	b.	neutralization of fatty	acids		d.	b,c						
.4. Dı	ıring		id dete	rgents, raw materials ar	e mix		14.7			- ,	t at a layer	
	a.	postdosing step			c.	slurry making step					V	
	b.	spray drying step			d.	none of these						
25. Pa	lmitic	c acid is										
	a.	CH ₃ (CH ₂) ₁₂ COOH			c.	CH ₃ (CH ₂) ₁₀ COOH	::::::::::::::::::::::::::::::::::::::				i to ende	7.00 s 70
	b.	CH ₃ (CH ₂) ₁₆ COOH			d.	none of these						
26.	Al	kylation of barbituric a	icid giv	/es								
	a.	hypnotic drug			c.	antibacterial drug	2					
	b.	anticancer drug			d.	antifungal drug				en e ^{le} m	W # 60	10
27.	Ac	cording to inorganic h	ypothe	sis, petroleum could be	form	ed in the form of						
	a.	carbides			c.	hydrocarbons						
	b.	carbon dioxide			d.	a,b		8	eg	ŝ	4.5.4.	in
	28.	is used to	reduce	engine knocking and in	ncreas	e the fuel's octane rating	g	: 6				
	a.	LPG			c.	Anti-knock agent						
	b.	Octane number			d.	None of these						
				حه	ب الصق	من فضلك إقلا		# 10gg=	#-0 x			(for * 77,8

29. 1	For $C_{14} - C_{20}$ fraction, it is used for		
a.	jet fuel	c.	lubricating oils
b.	diesel fuel	d.	ships fuel
30.	During Cativa process for the production of acetic acid	,	is used as catalyst
a.	Platinum	c.	Ruthenium
b.	Rhodium	d.	Iridium
31.	Phenylglycine is a starting material for the synthesis of		
a.	Ampicillin	c.	Amoxicillin
b.	Piprocaine	d.	Novocaine
32. the	Tedious, , energy sapping , rough , largely unscientific se are in accordance with	, inef	ficient, and yielding poor quality extracted oil. All
a.	conventional method	c.	solvent extraction method
b.	mechanical expression method	d.	old traditional method
33.	Partial oxidation of methane gives		
a.	H_2O	c.	Syn-gas
b.	CO ₂	d.	none of these
34.	Sulfonation of acetanilide followed by reaction with 2-	amin	opyrimidine and hydrolysis gives
a.	Sulphapyrimidine	c.	Sulphanilamide
b.	sulphathiazole	d.	Sildenafil
35. l eth	Reaction of benzyl cyanide with methyl-bis(2-chloroet anol gives	hyl)a	mine followed by hydrolysis and esterification with
a.	Tramadol	c.	Ibuprofen
b.	Pethidine	d.	Sildenafil
36. 1	n vegetable oil processing, degumming process is carr	ied o	ut using
a.	glycerol	c.	hot water
b.	Phosphoric acid	d.	sodium hydroxide
	سفحه	لب الد	من فضلك إة

	n viscous rayon production, wood pulp is treated with ilfide to form	aque	ous sodium hydroxide then treated with carbon
a.	Formaldehyde	c.	Acetic acid
b.	Methanol	d.	Xanthate
38. (One example for unsaturated fatty acids is		
a.	Lauric acid	c.	Palmitic acid
b.	Myristic acid	d.	none of these
	When propene reacts with chlorine and hypochlorous formed	acid f	followed by hydrolysis with sodium hydroxide
a.	Glycerol	c.	Acetic acid
b.	Methane	d.	Urea-formaldehyde resin
40.	Deodorizing step in vegetable oil refining is carried ou	ıt to r	emove volatile components, mainly
a.	soap	c.	aldehydes & ketones
b.	Glycerol	d.	free fatty acids

Mark $(\sqrt{})$ or (\times) (10 Marks)

- 1- In oil refining, small amount of NaOH is added to remove the remaining phospholipids.
- 2- Lidocaine is considered as a strong antibiotic.
- 3- Methane is an undesirable component because of its strong offensive odor, corrosion, air pollution by some of its compounds.
- 4- In oil refining, bleaching process is done by the addition of citric acid.
- 5- Brine solution is used during soap manufacturing for soap neutralization.
- 6- The starting material for pethidine preparation is aniline hydrochloride
- 7- The saponification process is an exothermic process.
- 8- Detergents are structurally like soaps but differ in the water-soluble part.
- 9- Aspirin inhibits the production of cell walls of bacteria.
- 10-Olefins are unstable and improve the anti-knock tendencies of gasoline.

من فضلك إقلب الصفحه

Part I: Inorganic Industrial Chemistry (50 Marks)

Question one:

- (A) Describe with chemical equations the reactions that occur to produce Only Two of the following:
- 1. H₂SO₄ by contact process
- 2. H₃PO₄ by wet process.
- 3. Syn gas by autothermal reforming of methane.
- (B) Mention three uses of each of the following (H₂SO₄ H₃PO₄ Syn gas).

Question two:

- (A) In the production of ammonia by Haber process in industry
 - 1) write the balanced chemical equation for the manufacture of ammonia.
 - 2) How much hydrogen would be in 400 liters (L) of gaseous mixture.
- (B) Choose the correct answer:
- 1- Carrying out this reaction at high temperature in the presence of a catalyst is in order to......
 - a) Speed up the conversion reaction to reach equilibrium soon, even though with low amount of ammonia
 - b) Increase the conversion to ammonia in each pass

 - d) b and c
- 2- The reaction 2NaCl + $2H_2O \rightarrow 2NaOH + Cl_2 + H_2$ is
 - a) Oxidation-reduction reaction
 - b) Electrochemical reaction.
 - c) Used in industry for coproduction of Cl₂ and caustic soda.
 - d) All the above.
- 3- In industrial production of phosphoric acid by the wet process, the crushed phosphate rock (appatite) is acidified with phosphoric acid before adding sulphuric acid. This is to prevent
 - a) Formation of soluble salts such as MgSO4 or iron sulphate in the produced phosphoric acid solution.
 - b) precipitation of other salts with gypsum.
 - c) formation of the Plaster gypsum layer on the surface of the crushed appatite.
 - d) all the above three
- (C) A plant that consumes 1170 tons of NaCl produces how many tons of NaOH.
- (D) Describe the main uses of NH₃ Cl₂ H₂.

إنتهت الأسئله كل الأمنيات بالتوفيق والنجاح

Prof. Dr Samer Kandel

Dr. Hamada Mandour

ME I	Tanta U	niversity, Faculty of Science,	Department of Chemistry
	[4 th Level	Final Exam of Solid Stat Chem-Bio, Micro, Bot, Ent.	te Chemistry Geo. Zol. and Mat Science
	course Title.	ب المددوجة – Sould State Chemistry	جميع الشي Code: CH4143
	nuary -2023	1 st Semester	Time: 2 Hours
Part(1	()		30 Mark

Answer the following:

- QI. True or False (\sqrt{x}), and if it is false correct it:20 Marks
 - 1) Graphite is Sp² hybridization and good insulator.
 - 2) Deliquescent materials are not vapor absorption matter.
 - 3) Stoichiometric defects are belonging to point defect type.
 - 4) Covalent crystals are bonded to each other by ionic bonds.
 - 5) Interstitial defects are belonging to stoichiometric ionic solids.
 - 6) Metal deficient defects are belonging to stoichiometric point defects.
 - 7) Smectic liquid crystal phase is not ordered crystals.
 - 8) Monoclinic crystals are maximum symmetry crystals type.
 - 9) Conduction in solids is hole mechanism-only.
 - 10) Liquid crystals (LC) are not obeying Bragg's law for X-ray diffraction.
 - 11) Conductors have no energy gab (Eg).
 - 12) n-type semiconductors are electron conduction mechanism.
 - 13) Diamagnetic materials have no unpaired electron.
 - 14) Polymerized crystalline arrays obey Bragg's law.
 - 15) Potassium chloride is belonging to Ionic solids.
 - 16) Population-inversion is the base of Laser-generation.
 - 17) Semiconductors conduction is enhancing via raising of temperature.
 - 18) Sol-Gel technique produces a microstructure better than other techniques.
 - 19) Annealing rates controlled in the formed crystalline phases.
- 20) Volume of lattice cell is greater than volume of atoms present within lattice.

			112
20 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0			STREET, STREET
خلف الورقه	5 K 6"	41: 411 51 10	
		تابع باقى الاستلك	The state of
	***********	تابع باقى الاسنله	THE REAL PROPERTY.

QII. Write the Scientific Term/or Sentence equal to each of the following; (10 Marks)

- Allotrope
- * Type of defects are present specially in ionic solids.
- * Laser.
- * The smaller ions are dislocated from its sites to interstitial sites.
- * Bragg's law.
- * Materials with the same chemical composition but differ in crystal form.
- * Capability and efficiency of crystal form to insert more atoms.
- * The zone in matter controlled in conduction mechanism.
- * Application of electricity to produce chemical reaction.
- * Crystalline Polymorphism.

Part (II)......20 Marks

QIII. Write a brief account on, Only Five Items:(10 marks)

- III.1. Photo-Voltaic Devices & Semiconducting Lasers.
- III.2. Polymorphism in iron/carbon.
- III.3. Atomic Packing efficiency (APF).
- III.4. Doping in semiconductors (n-type and p-type) semiconductors.
- III.5. Techniques applied for solid state synthesis.
- III.6. Different phases of liquid crystal.

QIV. Compare with drawing between each couple of the following;.....(10 Marks)

- 1. Crystalline and Amorphous solids.
- 2. Diamond and Graphite.
- 3. Frenkel and Schottky defects.
- 4. Polymorphism in carbon and calcium silicates.
- 5. Linear defects, Edge and Screw dislocations.

Best Wishes
Prof.Dr. Khaled M. Elsabawy
Professor of Materials Sciences
2023

Final Exam of Solid State Chemistry 2023- Examiner Prof.Dr. Khaled M. Elsabawy (2023)

		TANTA UN	IVERSITY- Faculty of Science -Departmen	t of Physics
Total (EXAMIFO	R SENIORS STUDENTS OF MATERIALS	SCIENCE
170.0	COURSE TITLE		Materials Design	COURSE CODE:MS4121
DATE:31	DECEMBER 2022	TERM: FIRST	TOTAL ASSESSMENT	
Wer the f	ollowing question		TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS

First Question:

[2 marks]

I) Cite the criteria that are important in the Selection consideration of materials.

[10Marks]

II) Using the selection consideration developed for minimum material mass and minimum cost, describe the acceptable candidates from the following Five Engineering Materials. [10Marks]

Material	(Mg/m^3)	Ty	<u>c</u>
Carbon fiber-reinforced composite(CF-RC)		(MPa)	(5/5)
Glass fiber-reinforced composite(GFRC)	1.5	1140	80
Aluminum aller (2004 Taller)	2.0	1060	40
Aluminum alloy (2024-T6)(Al.A)	2.8	300	15
Titanium alloy (Ti-6Al-4V)(Ti-AL.A)	4.4		13
4340 Steel.	7.0	525	110
o) Strangth (=) and D. L		780	5

Density (p), Strength (τ_f), and Relative Cost($\frac{1}{C}$) for Five Engineering Materials.

Second Question:

T 2000 marks}

- I) Find the shear stress of a helical spring has been constructed of wire having a circular cross section diameter (d), the coil center to center diameter (D), a compressive force (F) and force independent constant $k_w = 1 + \frac{1}{2c}$. [10Marks]
- II) Prove that the Stiffness of spring is $\left(\frac{G \cdot d}{8n \cdot C^3}\right)$. Where (G) and (C) are the rigidity and spring constant of coil material. [10Marks]

Third Question:

{ 30 marks}

- I) List and briefly explain the biocompatibility considerations relative to materials that are employed in artificial hip replacements.
- II) Compare between the specific properties of the three materials are employed in the femoral stem of the artificial hip replacement. [15Marks]

Forth Question:

{ 30 marks}

- I) Write the Required mechanical properties of the hip joint replaced components.
- [10Marks]
- II) List the Requirements of the Thermal Protection System Design on the Space Shuttle Orbiter.

[10Marks]

III) Write short notes about reinforced carbon-carbon used in the Designof Space Shuttle Orbiter.

[10Marks]

EXAMINERS DR. TALAAT MEAZ DR. REDA ELSHATER @ BEST WISHES

TANTA UNIVERSITY FACULTY OF SCIENCE DEPARTMENT OF PHYSICS

EXAMINATION FOR SENIOR (FOURTH YEAR) STUDENTS OF MATERIAL SCIENCE

	LAAN	EXAMINATION ON SENIOR (I SORTH TEAR) STOBENTS OF MATERIAL SCIENCE									
1083	COURSE TITLE:	El	ECTRON MICROSCOPY	COURSE CODE: MS4123							
DATE:	04/01/2023	TERM: FIRST	TOTAL ASSESSMENT MARKS:100	TIME ALLOWED: 2 HOURS							

ANSWER THE FOLLOWING QUESTIONS:

711	SWER THE FOLL	JULIG QUESTIC	<u> </u>			
Q1	(<u>20 Marks</u>)					
	A) Define the spatial		(<u>10 Marks</u>)			
	B) Write in brief about	the advantages and	disadvantages of S	EM regarding	sample prepar	
	7	*****	******	***		(<u>10Marks</u>)
Q2	(<u>25 Marks</u>) A) Discuss in brief about one of the com					pes and write (10 Marks)
	B) Draw a simple scl energetic electron be		3 N N N N N N N N N N N N N N N N N N N	esses in the in	nteraction be	tween an (15 Marks)
		*****	*******	****		
Q3	 Q3 (25 Marks) A) List the different types of lens defects and write briefly about one of them. 					
	B) Discuss in brief th	ne principle of elect	tron generation in	electron mic	roscopes.	(15 Marks)
		*****	*******	****		
Q4	- CHOOSE THE CO	RRECT ANSWE	R	(30 Marks, 2	marks each)
	The eye controls the a	amount of light read	ching the retina b	y varying the	e diameter of	f the aperture
) Receptor cells	B) Iris	C) Cornea	i	D) Pupil	
of	Two points separated a wavelength of 500 plution will be	150	0.50		-	
) 0.8 mm	B) 0.08 mm	C) 0.12 m	m	D) 0.16 mr	n
A) S	Chromatic aberration of Suitably combining it Providing different sui	with another lens			olishing of its	s two surfaces
A	What causes chromati A) Variation of the foc C) Difference in radii of	al length of the lens		B) Margin D) Central		



5) Chromatic aberration	in a lens is caused by		
A) Reflection	B) Dispersion	C) Interference	D) Diffraction
A) Thermionic emissi C) Photoelectric emiss	on	ectrons does not take place B) X-rays emission D) Secondary emissio	
7) Which of the followin A) Red	ng light is suitable for m B) Green	naximum resolution C) Blue	D) orange
,		,	_,8.
8) The resolving power A) 1 cm	of the unaided human e 200 μm	ye is C) 100 μm	400 nm
9) The process of emiss A) Thermionic emission C) Photoelectric emission	1	ot metal surfaces is called . B) X-rays emission D) Secondary emission	······································
	•	the metal when it is heated	
A) Electrons	B) Protons	C) Neutrons	D) Nucleon
11) Transmission electronA) Internal structure ofC) Surface structure of	fixed cells.	or high-magnification view B) Internal structure of D) Surface membranes	ive cells.
12) A microscope in w and focusing the scatter A) Scanning electron m	ed electrons with magne		beam through a specimen n microscope
C) Phase-contrast micro	oscope	D) Atomic force micros	cope
B) Evaporation fromC) Thermal excitation	etrons have very well-de m the surface that takes ion is not required	THE PARTIES AND ADDRESS OF THE PARTIES AND ADDRE	e -
14) In electron optics, the A) An electrostatic lens		or astigmatism is called C) An electron probe	D) A stigmator
15)is the ability A) Magnification	ty to distinguish betwee B) Ionization	n two adjacent objects. C) Spherical aberration	D) Resolving power

AL 1	T	ANTA UNIVERSIT	Y- Faculty of Science	Department o	f Physics
6			NIOR'S STUDENTS OF		
1962	COURSE TITLE:	Micro	oprocessing of Mater	ials	COURSE CODE: MS413
DATE:	2 JANUARY 2023	TERM: FIRST	TOTAL ASSESSMENT	MARKS: 100	TIME ALLOWED: 120 MIN
	er the following o				
		wers <u>clearly</u> in	the space provided.		tants and conversion
	are provided.			(25 marks/qu	iestion)
Questio		73			
	ON I: Choose the c		fl (1) has a sunit of	المانطين	an haam aanaantratian
	has a unit		mux (φ) has a unit of	while i	on beam concentration
ę.	nas a unit	•			
	a) # of atoms/cm ³ &	# of atoms/cm ²			
	b) # of atoms/cm ¹ &	# of atoms/cm ²			
	c) # of atoms/cm ² &				
	d) # of atoms/cm ⁻²		3		
2-	Dislocations in line	defects in crystal	s move by two primar	y mechanisms	,and glide.
į	a- climb	b- asce	ending	c- none of the	ese
3-	One of the advantag	es of the ion imp	lantation process is:		
	 a) Very expensive b) At high dose vasurface). 			(chemical so	urce pre-deposition on
	c) Ions damage the	semiconductor l	attice.		
	 d) Excellent doping and from wafer 	₩ .	chieved across the wa	fer (< 1% vari	ation across 12" wafer)
	Silicon On Insulate conventional wafers		provide better perform	nance for	speed circuits than
	a) High	b) low	c) intermediat	e	d) None of these
5-	In ion implantation a) ion energy and a b) atomic number c) target material d) all of these	mass	ected range, is a functi	on of	
6-					fications, depending on talline and amorphous

b) false

a) True

	energy(speed), char	ge, and mass o	of molecule				
	a) True	b) false					
8-	Lithography is a pri	nting process t	that uses phy	sical processe	s to create an	image.	
	a) True	b) False					
9-	Hg vapor lamps havinside a glass lamp.		which genera	te many spect	ral lines from	high intensity	plasma
	a) True	b) False					
10-	- In an ion implantat the desired impurit				through an a	$ngle \le 45^0$, and	i select
11	a) True - The line defects in	b) False crystals exte	nd in	dimension ar	nd the most of	common examp	ole is a
	a- One & dislocati	on b-t	wo & dissoci	ation	c- thre	ee & disintegrat	ion
	a) 1.817x10 ¹² cm ⁻² b) 1.130x10 ¹³ cm ⁻² d) None of these	concentration nm wafer using 23 μm, and ΔF 2, 76.06 S 2, 24.00 S 1.27 min	i is 1x10 ¹⁷ cr g 3 μA beam Rp= 0.0725 μ ed into P-typ	n ⁻³ is desired? current with a m).	? Also, the tirsingle ionized $C_{B} = 10^{16} / c$	me required import in the phosphorous? The contract of the co	olanting (HINT: of 10 ¹³ /
14	and Δ Rp= 0.0775 µ a) 3.2x10 ¹⁷ /cm ³ & b) 4.2x10 ¹⁷ /cm ³ & c) 5.2x10 ¹⁷ /cm ³ & d) 6.2x10 ¹⁷ /cm ³ &	um): 0.574 μm 0.274 μm 0.474 μm 0.374 μm					
	a- Isotropic	b- Isoth	ermal	c- non isc	otropic	d- all of these	

7- Diffusion is a time dependent process. Since, the diffusion movement is not based on kinetic

SECTION II: answer the following

- 1- If the temperature gradient in Czochralski silicon is 100°C/cm, calculate the maximum pull rate {HINT: thermal conductivity of silicon= 2.84 W/cm.K, latent heat of fusion of silicon is 430 cal/gm, and crystal density is 2.328 gm/cm³ }.
- 2- A silicon wafer that has 10¹⁶ cm⁻³ of boron is found to have a neutral vacancy concentration of 2 X 10¹⁰ cm⁻³ at some processing temperature and a singly ionized vacancy concentration of 10⁹ cm⁻³ at the same temperature. Determine the temperature and the activation energy of the charged vacancy with respect to the intrinsic level, (Ei) {activation energy of the neutral vacancy to be 2.6eV, α =4.73x10-4 eV/K, β =637 K}.

Ouestion two

- 1- In optical lithography systems, the light source plays important roles explain this when an excimer laser is used?
- 2- Write about dry and wet etching, also the three etching processes?
- 3- Explain in details the Deal---Grove Model of thermal oxidation?
- 4- A silicon wafer has a 2000-Å oxide on its surface, mathematically (a) How long did it take to grow this oxide at 1100 °C in dry oxygen? { HINT: B=0.0236 $(\mu m)^2/hr$, and B/A=0.169 $\mu m/hr$ } (b) The wafer is put back in the furnace in wet oxygen at 1000 °C. How long will it take to grow an additional 3000 Å of oxide {HINT: $B=0.314 (\mu m)^2/hr$, and $B/A=0.742 \mu m/hr$ }?

Ouestion three:

- 1- Write about the advantages of ion implantation?
- 2- A boron implant is performed into silicon at 100 keV. The boron beam is aligned with the silicon crystal so that channeling is present. Estimate the range of the channeled boron profile, by considering that electronic stopping is the only mechanism for slowing the boron ions.
- 3- Explain the effect of channeling on ion implantation?
- 4- If the analyzing magnet bends the ion beam through 90° and L= R = 60 cm, Find:
 - a- The displacement D that would be seen if B₁₀ is sent through the system when it is tuned for
 - b- The required field, if the extraction potential is 25 KV,

Questio6n Four:

- 1- You need a 300 mm diameter silicon ingot containing 5 x 10¹⁶ As atoms/cm³ and decide to use the Czochralski technique to grow it. You decide to: (1) grow at equilibrium growth conditions, (2) make the mass of the initial melt twice the mass of the final silicon ingot, (3) cut the wafers you need out of the middle of the final single crystal ingot, and (4) grow the final ingot a total of 1 meter in length. What concentration of As atoms should be in the melt?
- 2- A boule of B-doped single crystalline Si is pulled from the melt in a CZ process. Afterwards, it is sliced into wafers. The wafer taken from the top of the boule has a boron concentration of $3x10^{15}$ cm⁻³. What would the doping concentration of the wafer taken from the position corresponding to 90% of the initial melt solidified. The segregation coefficient for boron B in silicon Si is 0.8.
- 3- A 1000-Å gate oxide is required for some technology. It has been decided that the oxidation will be carried out at 1000°C, in dry oxygen. If there is no initial oxide, for how long should the oxidation be done? Is the oxidation in the linear regime, the parabolic regime, or between the two (HINT: at 1000° C in dry oxygen: $A=0.165 \mu m$, $B=0.0117 \mu m^2/hr$, and t=0.37 hr)?

EXAMINER

PROF. ALI IBRAHIM

O BEST WISHES O



TANTA UNIVERSITY **FACULTY OF SCIENCE**

	EXAMINATION FOR SENIORS (FORTH LEVEL) STUDENTS OF MATERIAL SCIENCE (SEMESTER 1)							
1969	COURSE TITLE:	INTRODU	CTION TO NANO-TECHNOLOGY	COURSE CODE: MS4163				
DATE:11	JANUARY, 2023	TERM: SUMMER	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS				

Answer the following Questions:

First questions: A) Define the following: {25 Marks }

(14 Marks).

- 1-Nanomaterials. 2-Nanotechnology. 3- Quantum-dots 4- Crystallite size 5-Bulk materials.
- B)-Reed the following and show which is true and which is false, and give the reason why? (11 Marks)
 - 1. There are no nano-scale structures in nature.
 - 2. Once nanotechnology is developed further, it will move to Pico-technology which structure is 1000 times smaller than nano structure.
 - 3. Nanotechnology has become familiar now because we can see what we have made.
 - 4. Surface force becomes stronger for nano-scale structure than its macro-scale counterpart.
 - 5. The color of gold colloids solutions is decided by the diameter of gold nanoparticles.
 - 6. The melting temperature of gold nanoparticles gets lower as the size becomes smaller.
 - 7. CdSe nanoparticles can generate the entire visible spectrum (400nm~780nm) by tuning the particle size. In another word, nanoparticles can emit rainbow colors.
 - 8. At the nanoscale, carbon has a new type of bonding which cannot be observed in bulk.
 - 9. Nanoparticle based fluorescence markers offer longer emission time.
 - 10. Material properties (e.g., melting temperature, energy band gap) will never change regardless of its size.
 - 11. Some metal nanoparticles can be used for anti-microbial (e.g., kill bacteria) application.

_	
Turn the page over	

Second question: {25Marks}.

A)- Write short notes about the unique size dependent properties of nanomaterial (give examples). (12 Marks).

B)- Discuss the fabrication methods of nano materials, (give examples)

(13 Marks).

Third question:

{25 Marks}

Discuss and show the advantage of using nanotechnology of the following fields:

1- Medicine.

(12 marks)

2- Environment.

(13 marks)

Fourth Question:

{25 Marks}

Discuss briefly and show the advantage of using nanotechnology of the following fields: 1-Clean Energy. (10 marks).

2- Information and communications.

(10 marks).

3- Consumer Goods.

(5 marks).

Examiner	Prof. Talaat M. Meaz	
A L		

A * 1

TANTA UNIVERSITY **FACULTY OF SCIENCE**

	90	DEPARTMENT OF PHYSICS					
	EXAMINA	TION FOR SENIORS (FO	ORTH LEVEL) STUDENTS OF MATERIAL	SCIENCE (SEMESTER 1)			
1959	COURSE TITLE:	INTRODU	CTION TO NANO-TECHNOLOGY	COURSE CODE: MS4163			
DATE:11	JANUARY, 2023	TERM: SUMMER	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS			

Answer the following Questions:

First questions: A) Define the following: {25 Marks }

(14 Marks).

- 1-Nanomaterials. 2-Nanotechnology. 3- Quantum-dots 4- Crystallite size 5-Bulk materials.
- B)-Reed the following and show which is true and which is false, and give the reason why? (11 Marks)
 - 1. There are no nano-scale structures in nature.
 - 2. Once nanotechnology is developed further, it will move to Pico-technology which structure is 1000 times smaller than nano structure.
 - 3. Nanotechnology has become familiar now because we can see what we have made.
 - 4. Surface force becomes stronger for nano-scale structure than its macro-scale counterpart.
 - 5. The color of gold colloids solutions is decided by the diameter of gold nanoparticles.
 - 6. The melting temperature of gold nanoparticles gets lower as the size becomes smaller.
 - 7. CdSe nanoparticles can generate the entire visible spectrum (400nm~780nm) by tuning the particle size. In another word, nanoparticles can emit rainbow colors.
 - 8. At the nanoscale, carbon has a new type of bonding which cannot be observed in bulk.
 - 9. Nanoparticle based fluorescence markers offer longer emission time.
 - 10. Material properties (e.g., melting temperature, energy band gap) will never change regardless of its size.
 - 11. Some metal nanoparticles can be used for anti-microbial (e.g., kill bacteria) application.

Turn the page over	
--------------------	--

Second question: A)- Write short notes about the unique size dependent properties of nanomaterial (give (12 Marks). examples). B)- Discuss the fabrication methods of nano materials, (give examples) (13 Marks). {25 Marks} Third question: Discuss and show the advantage of using nanotechnology of the following fields: (12 marks) 1- Medicine. (13 marks) 2- Environment.

{25Marks}.

{25 Marks} Fourth Question:

Discuss briefly and show the advantage of using nanotechnology of the following fields: (10 marks). 1-Clean Energy.

(10 marks). 2- Information and communications.

(5 marks). 3- Consumer Goods.

Prof. Talaat M. Meaz Examiner

Turn the page over

TANTA UNIVERSITY FACULTY OF SCIENCE DEPARTMENT OF PHYSICS EXAMINATION FOR FRESHMEN FOURTH LEVEL STUDENTS OF PHYSICS (MATERIAL SCIENCE) COURSE TITLE: (CERAMICS) COURSE CODE: MS4171 DATE: 18/1/2023 TERM: FIRST TOTAL ASSESSMENT MARKS: 100 TIME ALLOWED: 2 HOURS.

1) Define:

(20 Marks)

a. Bulk density

b. Piezoelectricity

c. Hard ferrites

d. Hysteresis

e. Coordination number

f. Magnetic susceptibility

2) Write Short Notes On:

(30 Marks)

- a. Electrical properties of ceramics.
- **b.** Factors affecting the cation distribution in spinel structure.
- c. Paramagnetic materials.
- d. Classification of ceramics based on their application (three only).
- e. Types of dielectric polarization.
- f. Types of ferrites (three only).

3) Put $(\sqrt{)}$ or (x) then correct the wrong answer: (20 Marks)

- a. Diamond has high index of refraction.
- b. The coordination number of cesium chloride structure (CsCl) is 6.
- c. Large polaron occurs when the effective mass of the electron is large.
- **d.** Oxygen positional parameter is the distance between oxygen ions and center of the cube.
- e. Vacancy in ceramics exists for both cations and anions.
- f. Ceramics have low density.
- g. The inversion parameter equals one for completely normal spinel ferrite.
- h. The unit cell of rock salt structure is FCC.
- i. In ferrimagnets, the magnetic moments of the A and B sublattices are equal.
- j. As the charge increases the size of the ion increases.
- 4) a. Compare between Frenkel and Schottky defect. (30 Marks)
 - **b.** X rays of λ = 0.1537 nm from a Cu target are diffracted from the (111) planes of an FCC metal. The Bragg angle is 19.2°. Calculate the Avogadro number if the density of the crystal is 2698 kg/m³ and the atomic weight 26.98 g/mol.

Good Luck Dr. Basant Salem

68.	TANTA UNIVERSITY- Faculty of Science - Department of Physics Physics & Biophysics - أمتحان المستوي الرابع					
-						
1501	COURSE TITLE:	Defec	tors & Accelerators	COURSE CODE: PH4163		
DATE:	28 - 12 - 2022	TERM: FIRST	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS		

Answer the following questions in Part A and Part B:

Part A: Chose the confect answer (firmank each	Tota	1-40 marks) Version: A	001
1) To detect the fast electrons, slowing down th	e fast	neutron in a moderating material is carried o	ut
before its detection as a	5 <u></u> 2	V	25 27
(a) thermal neutron		(c) charged particle	
(b) high energy neutron		(d) positive ion	
2) detectors can be sensitive to all types	s of ra	diation at all energies.	
(a) Some		(c) All	
(b) No		(d) Most	
3) The relatively thick dead layer in diffused ju	nction	diode is a particularly disadvantageous as th	e
energy lost in this layer	72=3		
(a) stays for long time in this area		, , , , , , , , , , , , , , , , , , , ,	
(b) produces electron-hole pairs		(d) goes unrecorded	
4) The strong forces have a range of the order of		cm.	
(a) 10^{-6}		(c) 10^{-13}	
(b) 10^{-9}		(d) 10^{-15}	
5) efficiency is the ratio of the number	of par	ticles detected to the number of particles	
incident on the detector surface.			
(a) Absolute detection		(c) Extrinsic detection	
(b) Intrinsic detection		(d) Geometrical	
6) In the accelerator, a homogeneous ma	agnetic	c field selects ions with a particular (e/m) to	
enters the accelerator.	_		
(a) Van de Graff		(c) Cyclotron	
(b) Cockcroft and Walton		(d) Tandem	
7) Ionizing radiation, passing through the space			
dissipates part or all of its energy by gener	ating		
(a) only electron		(c) electron-ion pairs	
(b) only positive ion		(d) scintillation light	
8) Neutrons are generally detected through			
(a) nuclear reactions		(c) molecular interactions	
(b) atomic scattering		(d) electrostatic forces	
9) acts in proportional counter as ioniz	ing ga	IS.	
(a) Argon		(c) Alcohol	
(b) Krypton		(d) Water	
10) At room temperature, the drift speed of ele	ctrons	is that for positive ions.	
(a) thousand times		(c) ten times	
(b) hundred times		(d) about the same as	

11) The good ereter consists of 1 1	1 0		
11) The accelerator consists of a belt magnisolated dome.	ade of	isolated material looped around two rollers a	ınd
(a) Cyclotron		(c) Van de Graff	
(b) Tandem		(d) Cockcroft and Walton	
12) Detector sensitivity is for a given		of radiation and energy	
(a) the capability of discriminating between		(c) the capability of producing a usable	
different types of radiation		signal	
(b) the ability to discriminate between closer		(d) the ability to determine the Energy of	82000
energies	0	the radiation	
13) are among the important influences	on the	operation of photomultiplier tubes.	
(a) Magnetic fields		(c) Exposure to ambient light	
(b) temperature		(d) all of the above	
14) In pulse chamber, may be meas			
(a) charge produced by the radiation may be		(c) motion of electrons induces a current	П
transformed into a pulse (b) motion of charge carriers induces a	_	on the electrodes	Ш
current on the electrodes		(d) All of the above	П
15) acts as quenching gas in Geiger Mul.	lon on		
(a) Argon		unter. (c) Alcohol	
(b) Krypton		(d) Water	Ц
16) semiconductor is formed with equa		(u) water	
(a) Pure		(c) Extrinsic	_
(b) Intrinsic			Ц
17) Gas proportional counters can be used to me		(d) compensated	\Box
the fill gas is usually	casure	e last neutrons through the recoil process who	re
(a) high-Z gas		(c) water vapor	
(b) medium-Z gas		(d) hydrogen or methane	
18) Normally, gas detectors are manufactured to		rate in	Ц
(a) only one region		(c) ionization and recombination regions	
(b) ionization and proportional regions		(d) all available regions	
19) are crystals of the alkali metals tha		rain a small concentration of an impurity	
(a) gas		(c) Inorganic scintillators	
(b) Plastic Scintillators		(d) Organic scintillators	
20) Ionization chamber is mainly used for meass	uring	(a) organic scrittingtors	<u>Ц</u>
(a) gamma-ray energy		(c) beta particles energy	П
(b) beta particles exposure		(d) gamma-ray exposure	
21) consist of planar molecules made i		penzenoid rings and formed by combining	
appropriate compounds.	-F	ormanoid rings and formed by combining	
(a) gas		(c) Inorganic scintillators	П
(b) Plastic Scintillators		(d) Organic scintillators	H
22) Photomultiplier tubes are		33.390.000.000	느
(a) gas tubes		(c) liquid tubes	
(b) fluid tubes		(d) vacuum tubes	\Box

23) In proportional region of gas-filed detectors,occurs very quickly near the anode. (a) non-localized avalanche	
(b) localized avalanche	
24) A widely used detector for slow neutrons is the proportional tube. (a) BCl ₃	
\Box (c) BF ₂	
$\begin{array}{c c} \hline \text{(b) BF}_3 & \hline \\ \hline \end{array} $ (d) He	
25) Elastic scattering of fast neutron by aims to transfer some portion of the neutron king energy to the target nucleus, resulting in a recoil nucleus.	
energy to the target nucleus, resulting in a recoil nucleus.	netic
(a) light nuclei	_
(b) heavy nuclei (d) free electrons	Ц
26) Limitations of scintillation detectors include	
(a) noise	_
(d) all of the above	Ц
27) In a gas-filled detector, both electrons and ions move under the influence of	\Box
(a) the electrical field	_
(b) their velocity	Ц
28) Except for silicon, semiconductors generally require before they can be operated.	
(C) heating to high towns and	1920-00-0
(d) no cooling or besting	
29) In semiconductor detectors, the passage of ionizing radiation creates	
(a) electrons (b) electron in the latter of	_
(d) positive ions	Ш
30) The forbidden energy bandgap in conductors, semiconductors, and insulators are EG1, EG2, a	<u>Ц</u>
i visition among them is	nd
(a) EG1 $<$ EG2 $<$ EG3 \Box (c) EG1 $>$ EG2 $>$ EG2	
(b) EG1 = EG2 = EG3 $\Box \qquad (d) EG3 < EG1 < EG2$	
31) band is above the Fermi level.	<u>Ц</u>
(a) Conduction (c) Valence	
(b) Low energy	님
32) The amount of ionization produced by radiation in a detector should be	<u>Ц</u>
ine energy if	
research the sensitive volume.	
(a) directly proportional (b) almost independent of	
(a) directly proportional (b) inversely proportional (c) almost independent of	
(a) directly proportional	
(a) directly proportional (b) inversely proportional (c) almost independent of (d) not related to (a) Van de Graff (b) Cyclotron	
(a) directly proportional	

3/) The accelerator uses remidly showing 1: 1 c					
(a) Van de Graff (b) Linear (c) Linear					
(a) Valide Glati		(c) linear			
(b) Cyclotron		(d) both (b) and (c)			
38) In semiconductor materials, the average en	erov r	equired to greate a shares and it	<u> </u>		
that required for gas ionization.	orgy It	squired to create a charge carrier is	than		
(a) 100 times larger		(c) 10 times smaller	П		
(b) 10 times larger		(d) 100 times smaller	H		
39) The spectrum of pulse heights will be	if a	particle loses all its energy in the detector.			
(a) a Gaussian peak with low energy tail		(c) a Gaussian peak with high energy tail			
(b) a Gaussian peak		(d) a linear function	H		
40) accelerators are now widely used in a variety of applications for scientific research					
applied physics, medicine, industrial proce	essing.	or applications for scientific research,			
(a) Charged particle		(c) Light			
(b) Electromagnetic		(d) Neutron			
			-		

	TANTA UNIVERSITY- Faculty of Science - Department of Physics Physics & Biophysics - أمتحان المستوي الرابع					
	DATE:	28 - 12 - 2022	TERM: FIRST	TOTAL ASSESSMENT MARKS: 100	TIME ALLOWED: 2 HOURS	

Part B: (Total 60 marks)

- 1) (a) What are the main components of the photomultiplier tube and what are their functions? (15 marks)
 - (b) What are the sources of the dark current in photomultiplier tubes? (5 marks)
- 2) (a) Discuss and sketch the alpha-particles' spectrum from a large BF₃ tube and then explain the wall effect and it could be overcome. (10 marks)
 - (b) Sketch and explain the relationship between charges collected and applied voltage for gas counters. (10 marks)
- 3) (a) Explain the mechanism of the scintillation process in organic scintillators. Use drawing for the energy levels. (10 marks)
 - (b) Give an account of the acceleration process of ONLY one, either the linear accelerator OR the Cyclotron. (10 marks)